

2SJ318(L), 2SJ318(S)

Silicon P-Channel MOS FET

HITACHI

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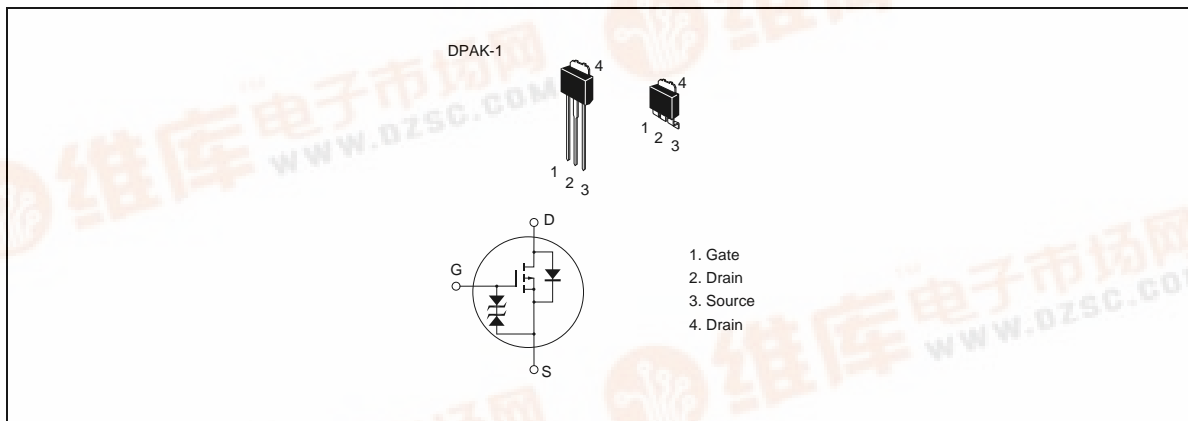
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device can be driven from 5 V source
- Suitable for switching regulator, DC-DC converter

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	-20	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-5	A
Drain peak current	$I_{D(pulse)}^{*1}$	-20	A
Body to drain diode reverse drain current	I_{DR}	-5	A
Channel dissipation	Pch^{*2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
 2. Value at $T_c = 25^\circ C$

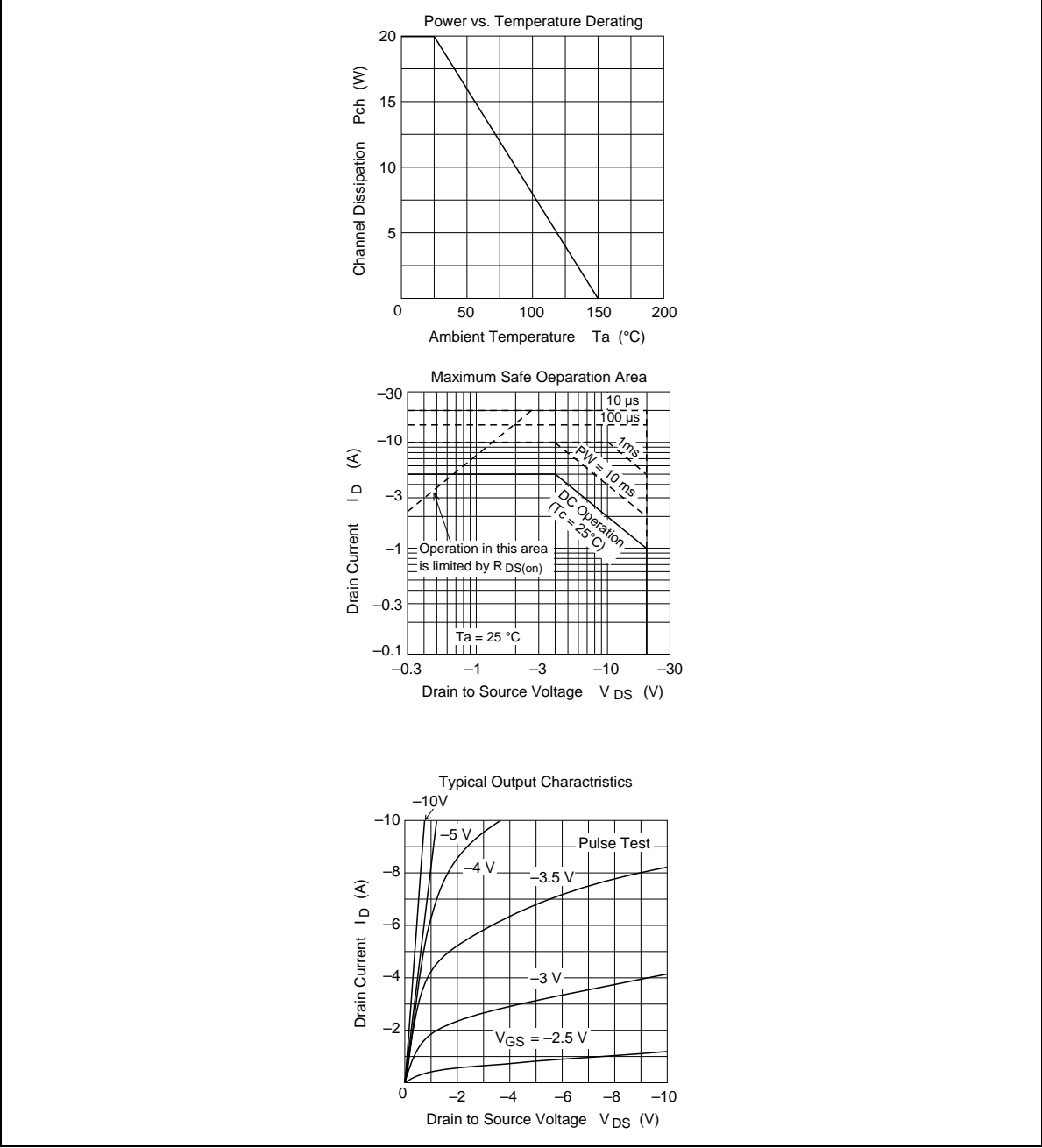
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-20	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-100	μA	$V_{DS} = -16 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.25	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.09	0.13	Ω	$I_D = -3 \text{ A}$, $V_{GS} = -10 \text{ V}^{*1}$
		—	0.14	0.19	Ω	$I_D = -3 \text{ A}$, $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.5	5.5	—	S	$I_D = -3 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	Ciss	—	580	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$,
Output capacitance	Coss	—	520	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	Crss	—	215	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = -3 \text{ A}$, $V_{GS} = -10 \text{ V}$,
Rise time	t_r	—	60	—	ns	$R_L = 3.3 \Omega$
Turn-off delay time	$t_{d(off)}$	—	75	—	ns	
Fall time	t_f	—	75	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.1	—	V	$I_F = -5 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	65	—	μs	$I_F = -5 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu s$

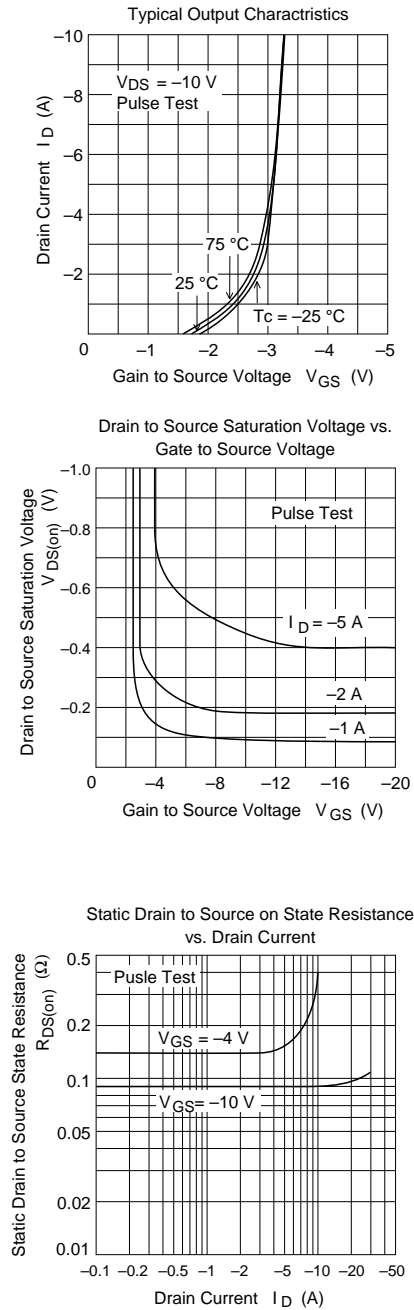
Note 1. Pulse test

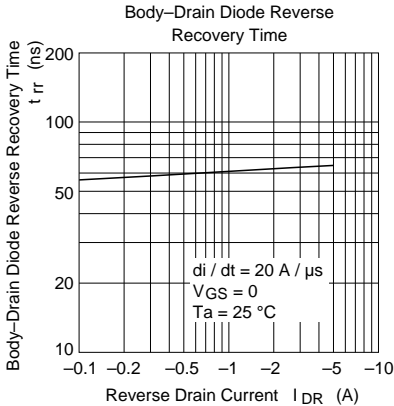
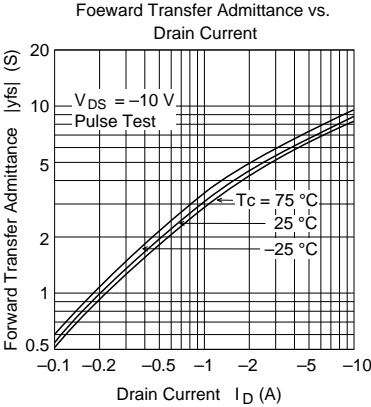
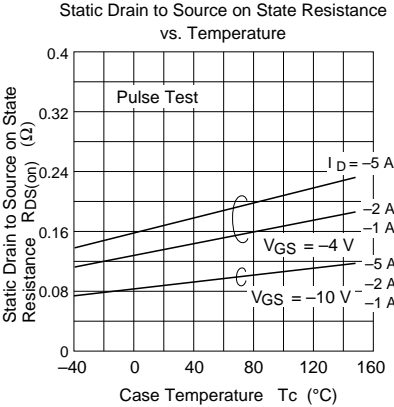


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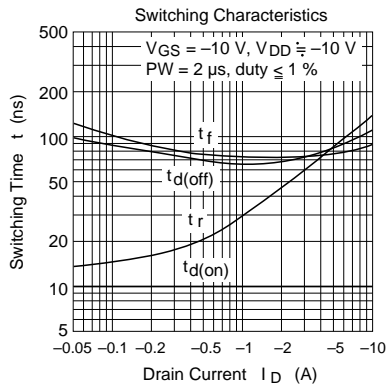
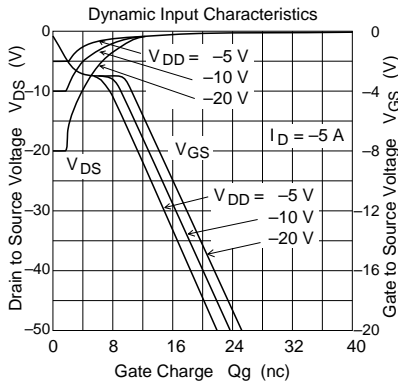
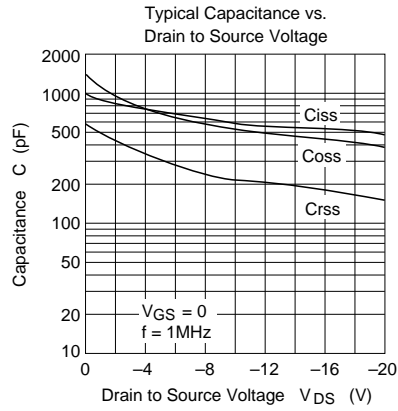


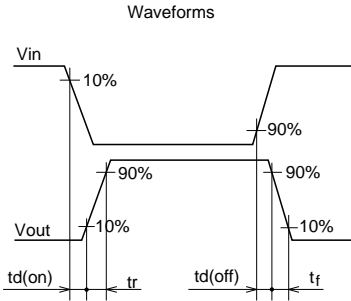
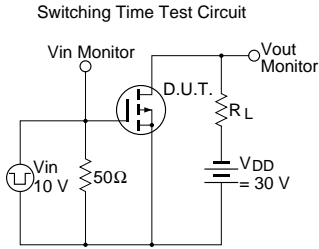
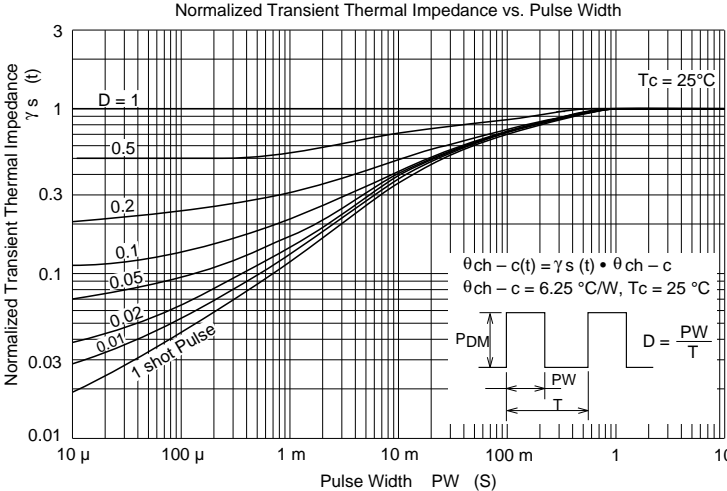
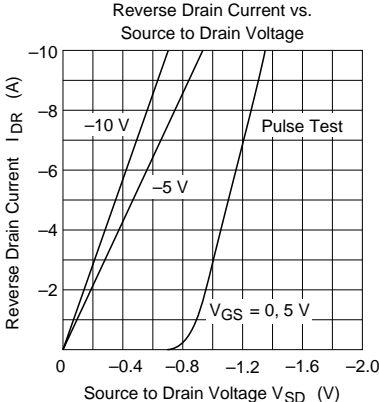
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